

LBSS139DW1T1G

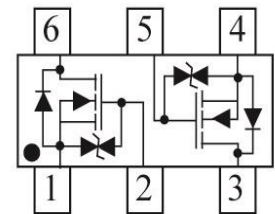
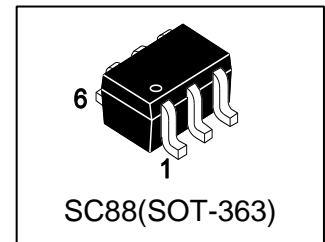
S-LBSS139DW1T1G

Power MOSFET

200 mAmps, 50 Volts N-Channel SC-88

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low threshold voltage ($V_{GS(th)}$: 0.5V...1.5V) makes it ideal for low voltage applications.
- ESD Protected:1500V



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS139DW1T1G	J2	3000/Tape&Reel
LBSS139DW1T3G	J2	10000/Tape&Reel

3. MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DSS}	50	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current			mAdc
– Continuous $T_A = 25^\circ\text{C}$	I_D	200	
– Pulsed ($t_p \leq 10\mu\text{s}$)	I_{DM}	800	

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	PD	380	mW
		3.05	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient(Note 1)	$R_{\theta JA}$	328	$^\circ\text{C/W}$
Junction and Storage temperature	T_J, T_{stg}	$-55 \sim +150$	$^\circ\text{C}$
Maximum Lead Temperature for Solde Purposes, for 10 seconds	TL	260	$^\circ\text{C}$

1. FR-4 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)
OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250μAdc)	VBRDSS	50	-	-	Vdc
Zero Gate Voltage Drain Current (VGS = 0, VDS = 25 Vdc) (VGS = 0, VDS = 50 Vdc)	IDSS	-	-	0.1 0.5	μAdc
Gate–Body Leakage Current, Forward (VGS = 20 Vdc)	IGSSF	-	-	10	μAdc
Gate–Body Leakage Current, Reverse (VGS = - 20 Vdc)	IGSSR	-	-	-10	μAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 1.0mAdc)	VGS(th)	0.5	-	1.5	Vdc
Static Drain–Source On–State Resistance (VGS = 2.75 Vdc, ID < 200 mAdc, TA = -40°C to +85°C) (VGS = 5.0 Vdc, ID = 200 mAdc)	RDS(on)	-	5.6	10 3.5	Ohms
Forward Transconductance (VDS = 25 Vdc, ID = 200 mAdc, f = 1.0 kHz)	gfs	100	-	-	mS

DYNAMIC CHARACTERISTICS

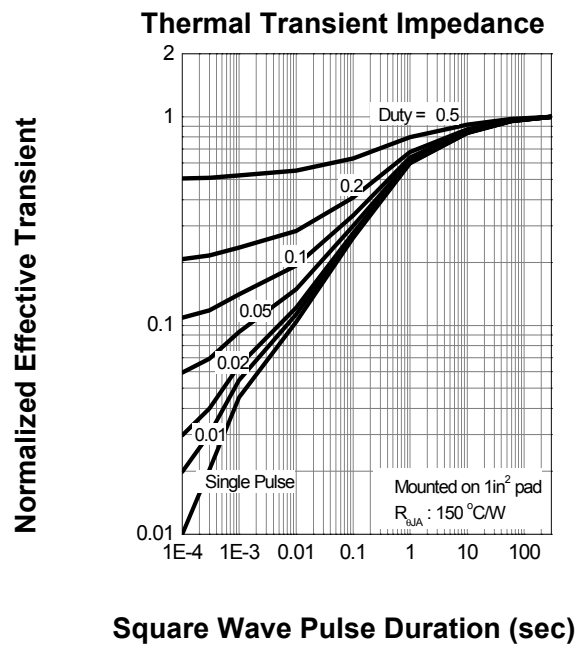
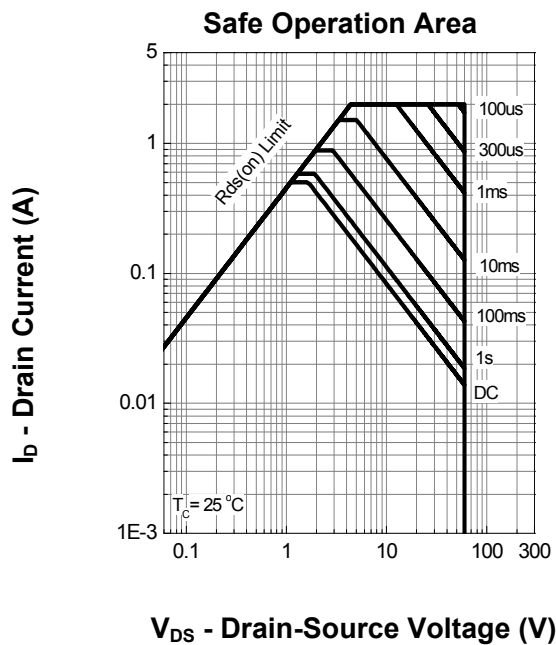
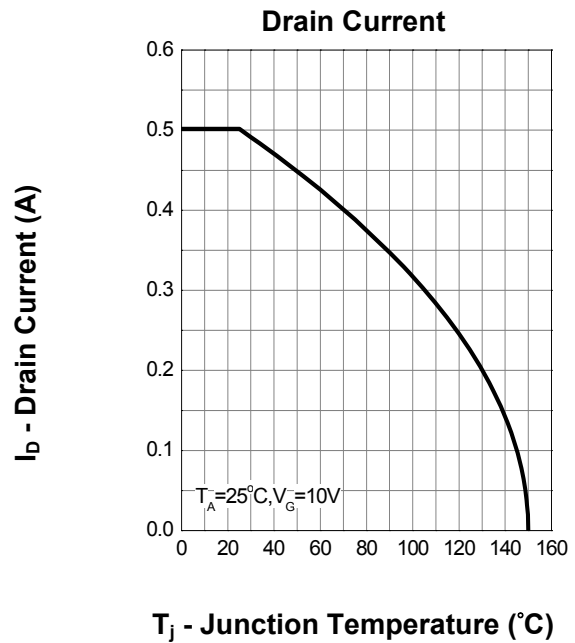
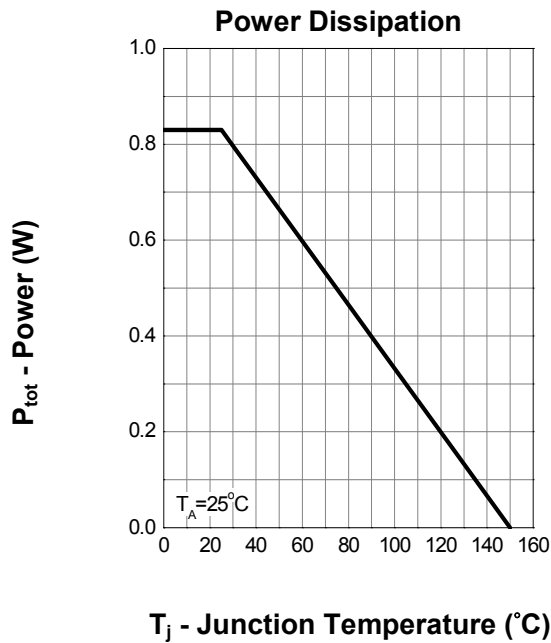
Input Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	22.8	-	pF
Output Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Coss	-	3.5	-	pF
Reverse Transfer Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Crss	-	2.9	-	pF

SWITCHING CHARACTERISTICS

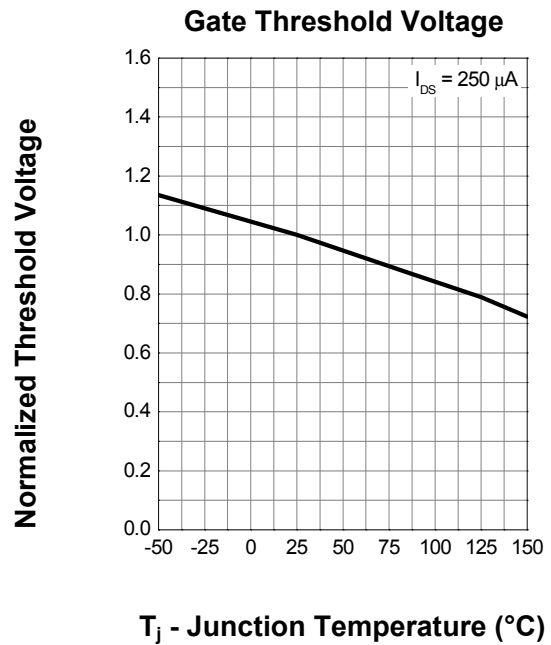
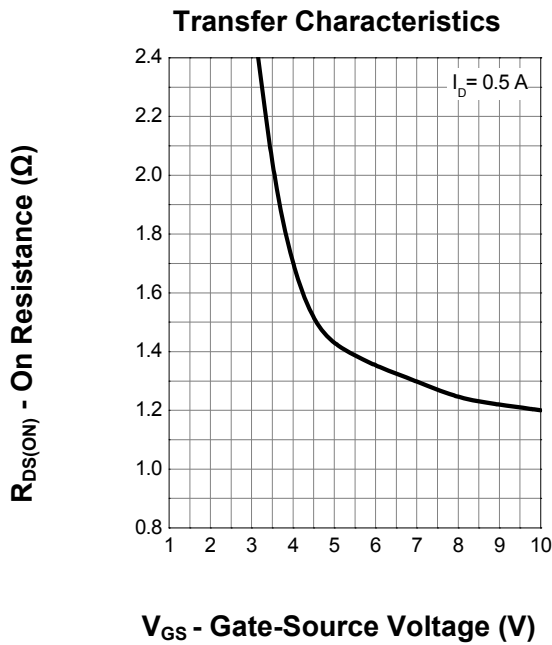
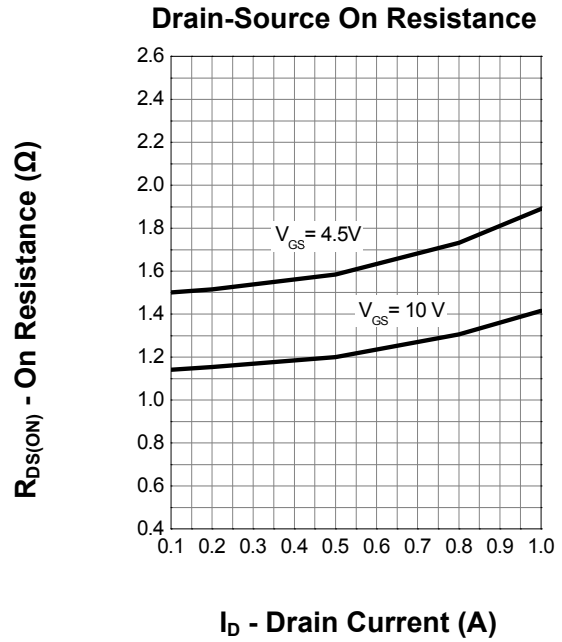
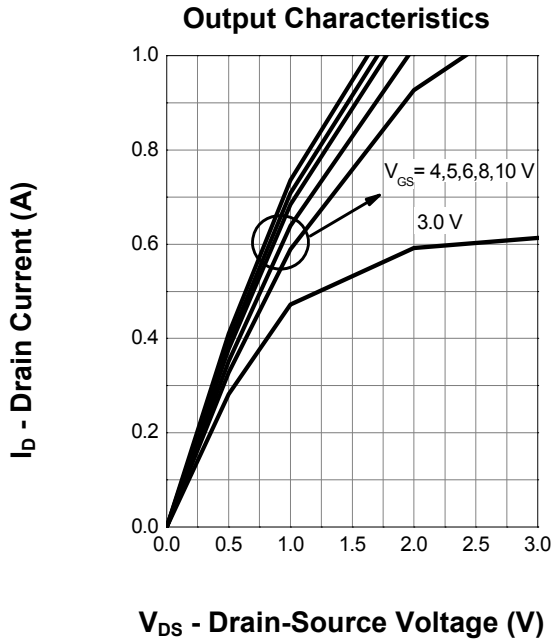
Turn-On Delay Time	(VDD = 30 Vdc , VGEN = 10 V, RG =25Ω ,RL =60 Ω, ID =500 mAdc)	td(on)	-	3.8	-	ns
Turn-Off Delay Time		td(off)	-	19	-	

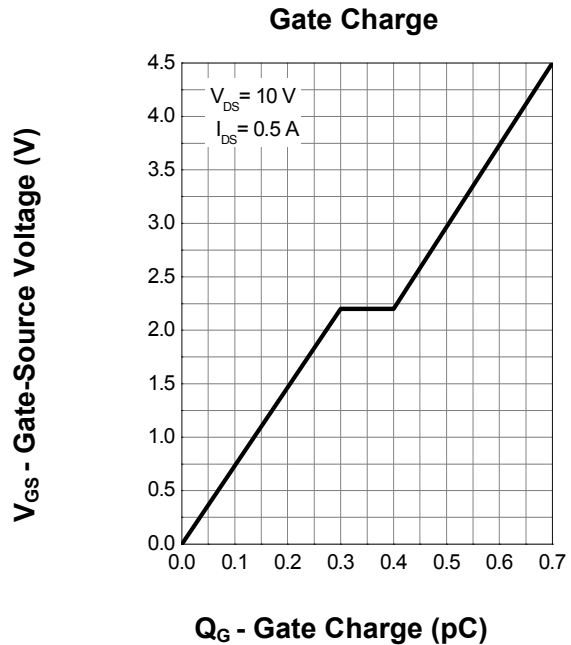
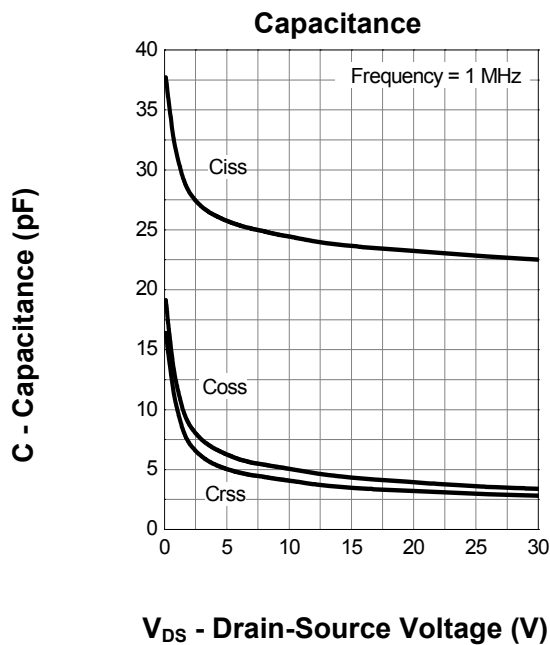
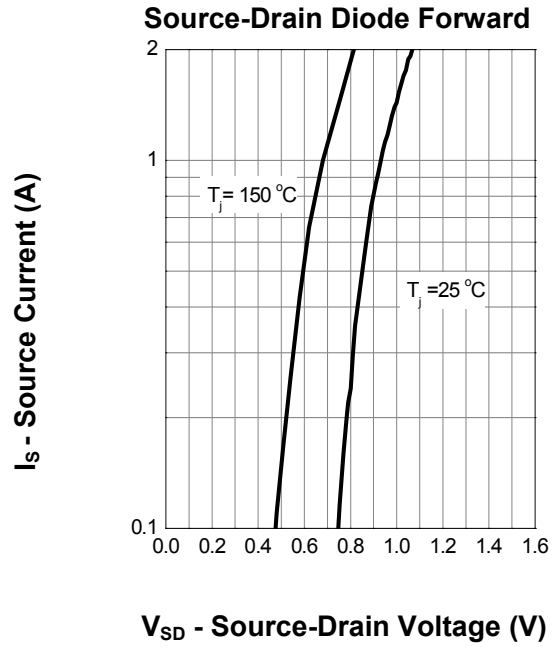
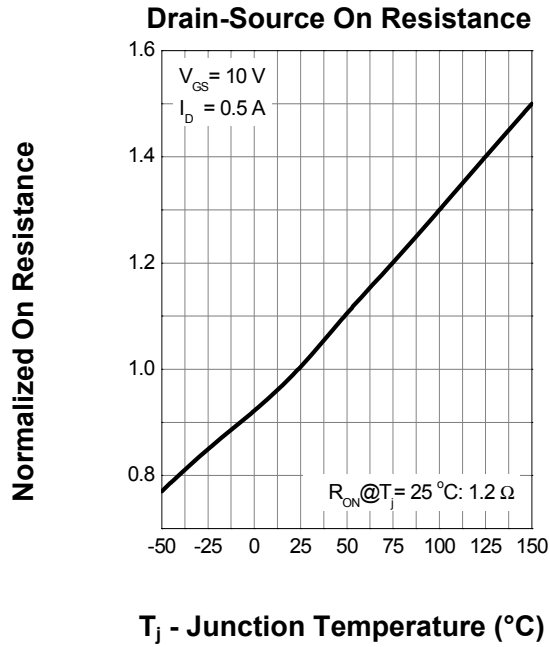
2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

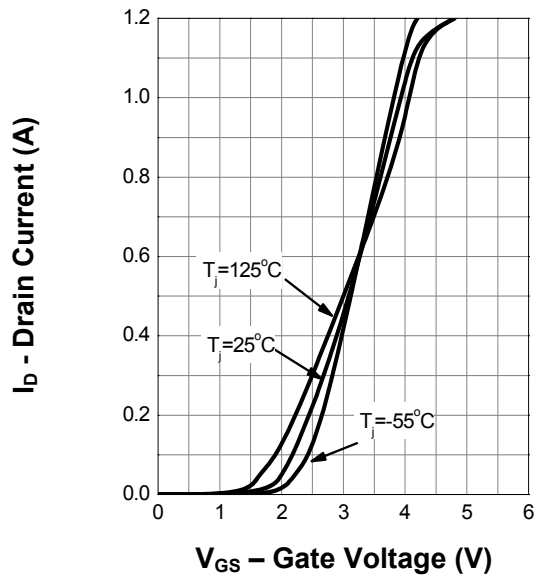
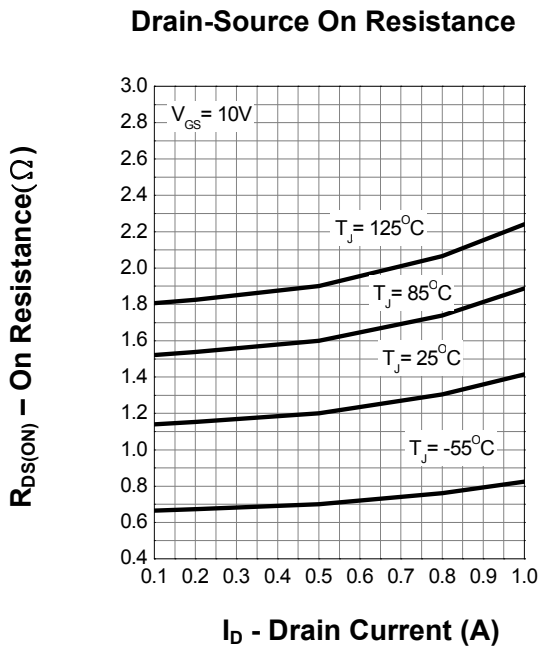
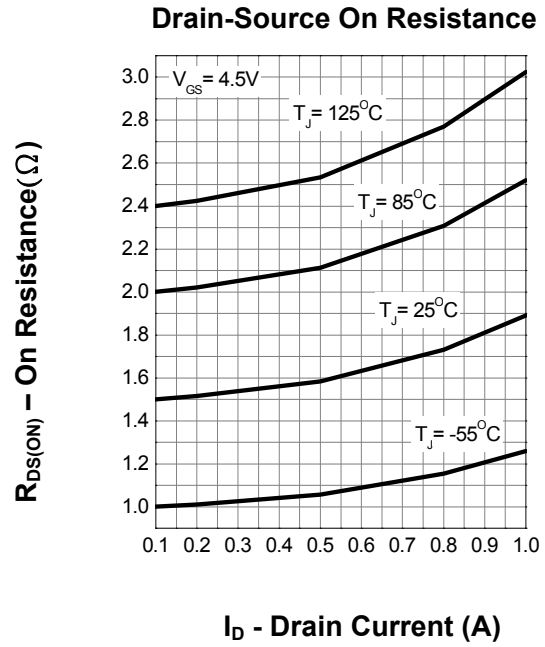
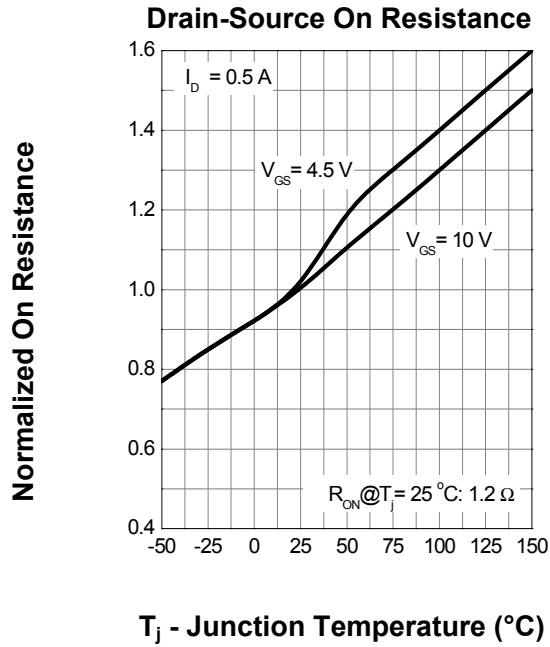
6. ELECTRICAL CHARACTERISTICS CURVES



6. ELECTRICAL CHARACTERISTICS CURVES(Con.)



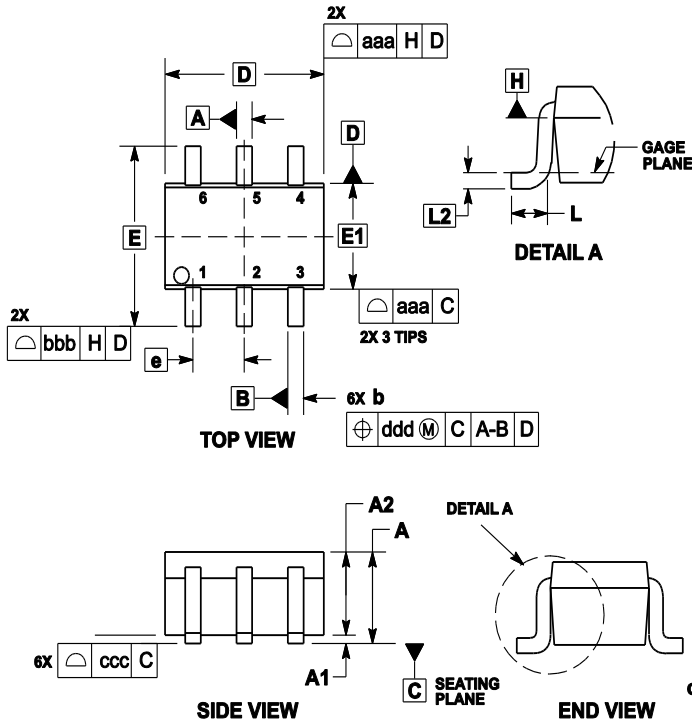
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7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.01
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.07	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.01		
bbb	0.30			0.01		
ccc	0.10			0.00		
ddd	0.10			0.00		

8. SOLDERING FOOTPRINT

